

**INFORMATION DISCLOSURE
CITATION**

ATTY. DOCKET NO.

160-399

DIVISIONAL OF SERIAL NO.

10/229,067

APPLICANT

Nakamura et al

(Use several sheets if necessary)

FILING DATE

GROUP

November 24, 2003

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,684,309	11/1997	McIntosh et al	257	14	
	4,862,471	8/1989	Pankove	372	45	
	5,646,953	7/1997	Naito et al	372	46	
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	5,959,307	9/1999	Nakamura et al	257	14	
	5,679,965	10/1997	Schetzina	257	103	
	5,412,226	5/1995	Rejman-Greene et al	257	21	
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	5,689,123	11/1997	Major et al	257	190	
	6,005,258	12/1999	Manabe et al	257	13	
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FOREIGN PATENT DOCUMENTS

TRANSLATION

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
0 675 552 A1	10/1995	Europe				
6-21511	1/1994	Japan				
3-290984	4/1990	Japan				
4-218994	8/1992	Japan				
7-074431	3/1995	Japan				X
61-156788	7/1986	Japan				X
08/290218	10/1996	Japan				X
6-268257	6/1994	Japan				X
6-177423	6/1994	Japan				X
7-235723	9/1995	Japan				
4-68579	3/1992	Japan				
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6-177423	6/1994	Japan				
6-21511	1/1994	Japan				
6-237039	8/1994	Japan				
7-297447	11/1995	Japan				
6-232451	8/1994	Japan				X

OTHER DOCUMENTS (including Auth , Titl , Date, Pertinent pages, tc.)

*Examiner		Date Considered
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Form PTO-FB-A820 (Also PTO-1449)

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	Narukawa et al Phys. Rev. B Vol. 55, No. 4, pp R1938-1941-1/97 Recombination dynamics of localized excitons in $In_{0.20}Ga_{0.80}N$ - $In_{0.05}Ga_{0.95}N$ multiple quantum wells
	Narukawa et al Appl. Phys. Lett. 70 (8), pp 981-983, 2/1997 Role of self-formed InGaN quantum dots for exciton localization in the purple laser diode emitting at 420 nm
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	Nakamura et al Appl. Phys. Lett. 69 (11), pp. 1568-1570, 9/96 Optical gain and carrier lifetime of InGaN multi-quantum well structure laser diodes
	Jpn J. Appl. Phys. Vol. 34 (1995) pp. L1332-L1335, Part 2, No. 10B, 15 Oct. 1995, "Superbright Green InGaN Single-Quantum-Well-Structure Light-Emitting Diodes"
	Technical Report of IEICE, ED96-100, CPM96-78 (1996-10), pp. 15-21
	Technical Report of IEICE, ED96-110, CPM96-88 (1996-10), pp. 81-88
	Appl. Phys. Lett., 38 (11) June 1981 pp 835-837

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